



DMT10H072LFV

100V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
	$62m\Omega @ V_{GS} = 10V$	20A
100V	77mΩ @ V _{GS} = 6V	16A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

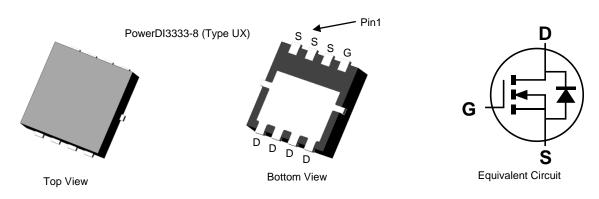
- **Power Management Functions**
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.

Features and Benefits

- Low R_{DS(ON)} Ensures On State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher **Density End Products**
- Occupies just 33% of the Board Area Occupied by SO-8 **Enabling Smaller End Product**
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.072 grams (Approximate)



Ordering Information (Note 4)

	Part Number	Case	Quantity per Reel	
	DMT10H072LFV-7	PowerDI3333-8 (Type UX)	2,000/Tape & Reel	
	DMT10H072LFV-13	PowerDI3333-8 (Type UX)	3,000/Tape & Reel	
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.				

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2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

4. For packaging details, go to our website athttps://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



T72= Product Type Marking Code YYWW = Date Code Marking \overline{YY} = Last Two Digits of Year (ex: 19 = 2019) WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	100	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current, $V_{GS} = 10V$ (Note 5)	T _A = +25°C T _A = +70°C	ID	4.7 3.7	А
Continuous Drain Current $V_{GS} = 10V$ (Note 6)	T _C = +25°C T _C = +70°C	ID	20 16	A
Pulsed Drain Current (10µs Pulse, T _C =+25°C, Package Limited)	I _{DM}	80	А	
Pulsed Body Diode Current (10µs Pulse, T _C =+25°C, Package Lim	I _{SM}	80	А	
Maximum Body Diode Continuous Current	ls	2	А	
Avalanche Current (Note 9), L=0.1mH	I _{AS}	6	А	
Avalanche Energy (Note 9), L=0.1mH	E _{AS}	1.8	mJ	

Thermal Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	2	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	61	°C/W
Total Power Dissipation (Note 6)	PD	37.8	W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	3.3	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	Symbol		, iyp	max	Unit		
Drain-Source Breakdown Voltage	BV _{DSS}	100	-	-	V	$V_{GS} = 0V, I_{D} = 250 \mu A$	
Zero Gate Voltage Drain Current	IDSS	-	-	1	μA	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1.5	-	2.8	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
		-	50.6	62	mΩ	$V_{GS} = 10V, I_D = 4.5A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	-	61.2	77		$V_{GS} = 6V, I_D = 4A$	
	R _{DS(ON)}	-	82.5	109	mΩ	V _{GS} = 4.5V, I _D = 2.7A	
Diode Forward Voltage	V _{SD}	-	0.76	1	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)						·	
Input Capacitance	C _{iss}	-	228	-	pF	V _{DS} = 50V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	-	89.3	-	pF		
Reverse Transfer Capacitance	C _{rss}	-	2.5	-	pF		
Gate Resistance	Rg	-	8.2	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qq	-	2.5	-	nC		
Total Gate Charge (V _{GS} = 10V)	Qq	-	4.5	-	nC		
Gate-Source Charge	Q _{gs}	-	0.6	-	nC	$V_{DS} = 50V, I_D = 4.5A$	
Gate-Drain Charge	Q _{ad}	-	1.3	-	nC	1	
Turn-On Delay Time	t _{D(ON)}	-	3.0	-	ns		
Turn-On Rise Time	t _R	-	3.1	-	ns	$V_{DS} = 50V, R_L = 11Ω$ $V_{GS} = 10V, R_{GEN} = 3Ω$	
Turn-Off Delay Time	t _{D(OFF)}	-	12.3	-	ns		
Turn-Off Fall Time	tF	-	4.3	-	ns	7	
Reverse Recovery Time	t _{RR}	-	22.9	-	ns		
Reverse Recovery Charge	Q _{RR}	-	45.2	-	nC	$I_F = 4.5A$, di/dt = 300A/µs	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

6. Thermal resistance from junction to soldering point (on the exposed drain pad).

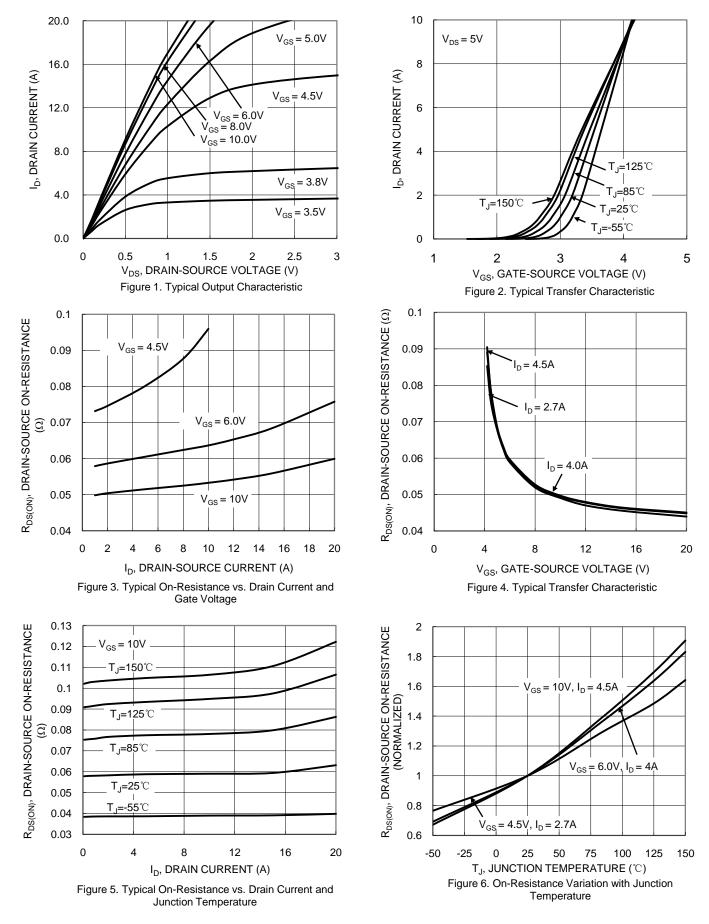
7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.

9. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.



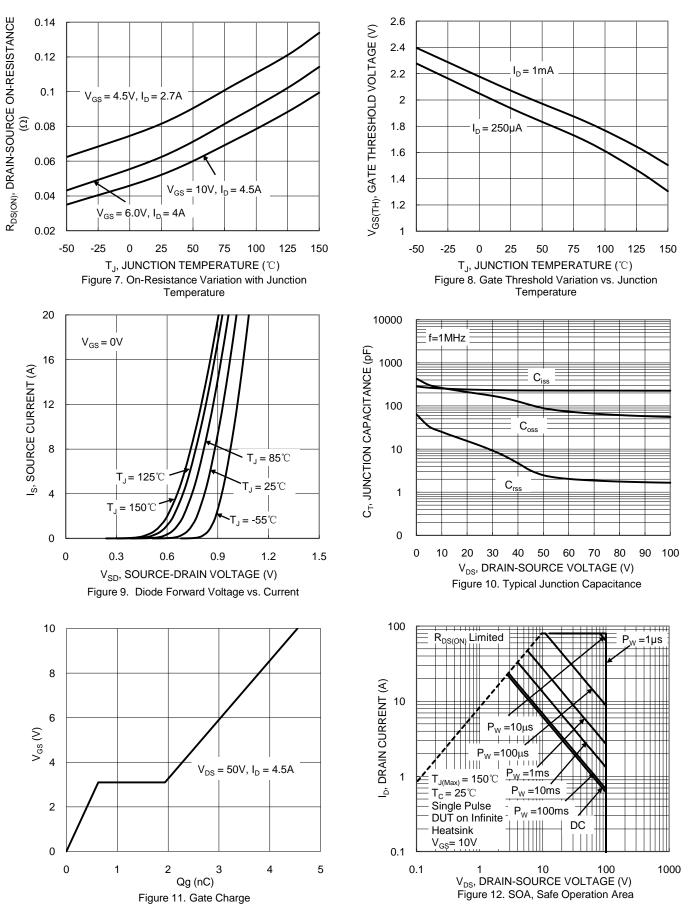
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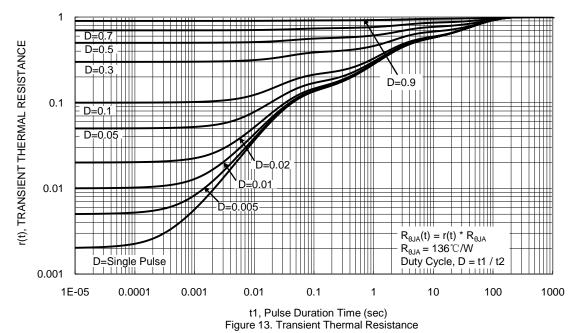


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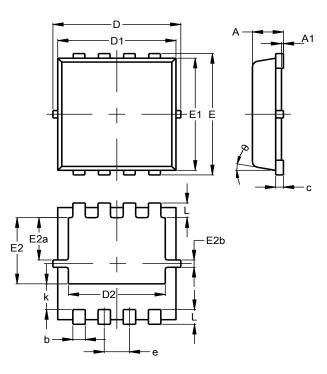




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)

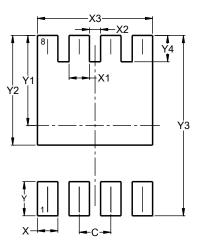


PowerDI3333-8					
(Type UX)					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
С	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
ш	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E2a	0.95	1.35	1.15		
E2b	0.10	0.30	0.20		
е	0.65 BSC				
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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